74HC1G08-Q100; 74HCT1G08-Q100

2-input AND gate Rev. 2 — 16 August 2012

Product data sheet

General description 1.

74HC1G08-Q100 and 74HCT1G08-Q100 are high-speed, Si-gate CMOS devices. They provide a 2-input AND function.

The HC device has CMOS input switching levels and supply voltage range 2 V to 6 V.

The HCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

The standard output currents are half of those of the 74HC08-Q100 and 74HCT08-Q100.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

Features and benefits 2.

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ♦ MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

Ordering information 3.

Table 1. **Ordering information**

Type number	Package									
	Temperature range	Name	Description	Version						
74HC1G08GW-Q100	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads;	SOT353-1						
74HCT1G08GW-Q100			body width 1.25 mm							
74HC1G08GV-Q100	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753						
74HCT1G08GV-Q100	_									



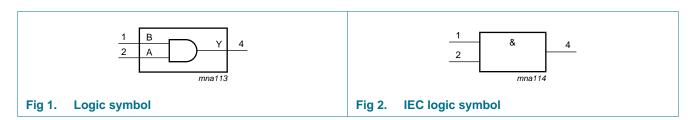
4. Marking

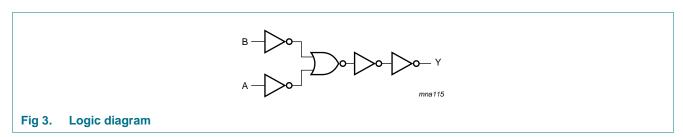
Table 2. Marking codes

Type number	Marking[1]
74HC1G08GW-Q100	HE
74HCT1G08GW-Q100	TE
74HC1G08GV-Q100	H08
74HCT1G08GV-Q100	T08

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

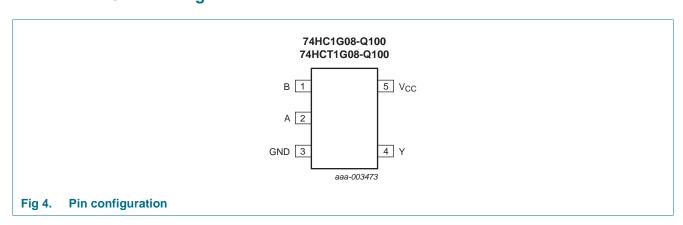
5. Functional diagram





6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
В	1	data input
Α	2	data input
GND	3	ground (0 V)
Υ	4	data output
V _{CC}	5	supply voltage

7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level

Input		Output
Α	В	Υ
L	L	L
L	Н	L
Н	L	L
Н	Н	Н

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [1]

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	-	±20	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	-	±20	mA
Io	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±12.5	mA
I _{CC}	supply current		-	25	mA
I_{GND}	ground current		-25	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T_{amb} = -40 °C to +125 °C	[2] -	200	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

^[2] Above 55 $^{\circ}$ C the value of P_{tot} derates linearly with 2.5 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC10	908-Q100)	74HCT1	00	Unit	
			Min	Тур	Max	Min	Тур	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise	$V_{CC} = 2.0 \text{ V}$	-	-	625	-	-	-	ns/V
	and fall rate	V _{CC} = 4.5 V	-	-	139	-	-	139	ns/V
		$V_{CC} = 6.0 \text{ V}$	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions	-40	°C to +	85 °C	-40 °C	Unit	
			Min	Тур	Max	Min	Max	
74HC1G0	8-Q100		'	'		'		
V_{IH}	HIGH-level input	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	V
	voltage	V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	V
		$V_{CC} = 6.0 \text{ V}$	4.2	3.2	-	4.2	-	V
V_{IL}	LOW-level input	V _{CC} = 2.0 V	-	8.0	0.5	-	0.5	V
	voltage	V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	V
		$V_{CC} = 6.0 \text{ V}$	-	2.8	1.8	-	1.8	V
V _{OH}	HIGH-level output	$V_I = V_{IH}$ or V_{IL}						
	voltage	$I_O = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	V
		$I_{O} = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	V
		$I_O = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	V
		$I_{O} = -2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.13	4.32	-	3.7	-	V
		$I_{O} = -2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.63	5.81	-	5.2	-	V
V_{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL}						
	voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	V
		$I_O = 20 \mu A$; $V_{CC} = 4.5 \text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.33	-	0.4	V
		$I_O = 2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.33	-	0.4	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	1.0	-	1.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	10	-	20	μА
Cı	input capacitance		-	1.5	-	-	-	pF

 Table 7.
 Static characteristics ...continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions	-40	°C to +	85 °C	-40 °C	-40 °C to +125 °C		
			Min	Тур	Max	Min	Max		
74HCT1G	08-Q100		'	'	'		'	'	
V _{IH}	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	1.6	-	2.0	-	V	
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	1.2	8.0	-	0.8	V	
V_{OH}	HIGH-level output	$V_I = V_{IH}$ or V_{IL}							
	voltage	$I_O = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	V	
		$I_{O} = -2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.13	4.32	-	3.7	-	V	
V_{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL}							
	voltage	$I_O = 20 \mu A$; $V_{CC} = 4.5 V$	-	0	0.1	-	0.1	V	
		$I_O = 2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.33	-	0.4	V	
l _l	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	1.0	μΑ	
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	10	-	20	μΑ	
ΔI_{CC}	additional supply current	per input; $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V};$ $V_I = V_{CC} - 2.1 \text{ V};$ $I_O = 0 \text{ A}$	-	-	500	-	850	μА	
Cı	input capacitance		-	1.5	-	-	-	pF	

11. Dynamic characteristics

Table 8. Dynamic characteristics

GND = 0 V; $t_r = t_f \le 6.0$ ns; All typical values are measured at $T_{amb} = 25$ °C. For test circuit see <u>Figure 6</u>

Symbol	Parameter	Conditions		-40	°C to +8	35 °C	-40 °C	-40 °C to +125 °C			
				Min	Тур	Max	Min	Max			
74HC1G	08-Q100				'	'	'				
t _{pd}	propagation delay	A and B to Y; see Figure 5	<u>[1]</u>								
		$V_{CC} = 2.0 \text{ V}; C_L = 50 \text{ pF}$		-	25	115	-	135	ns		
		$V_{CC} = 4.5 \text{ V}; C_L = 50 \text{ pF}$		-	9	23	-	27	ns		
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	7	-	-	-	ns		
		$V_{CC} = 6.0 \text{ V}; C_L = 50 \text{ pF}$		-	8	20	-	23	ns		
C_{PD}	power dissipation capacitance	$V_I = GND \text{ to } V_{CC}$	[2]	-	19	-	-	-	pF		
74HCT10	G08-Q100										
t _{pd}	propagation delay	A and B to Y; see Figure 5	<u>[1]</u>								
		$V_{CC} = 4.5 \text{ V}; C_L = 50 \text{ pF}$		-	11	23	-	27	ns		
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	11	-	-	-	ns		

 Table 8.
 Dynamic characteristics ...continued

GND = 0 V; $t_r = t_f \le 6.0$ ns; All typical values are measured at $T_{amb} = 25$ °C. For test circuit see Figure 6

Symbol	Parameter	Conditions		–40 °C to +85 °C			–40 °C to	Unit	
				Min	Тур	Max	Min	Max	
C_{PD}	power dissipation capacitance	$V_I = GND \text{ to } V_{CC} - 1.5 \text{ V}$	[2]	-	21	-	-	-	pF

- [1] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [2] C_{PD} is used to determine the dynamic power dissipation P_D (μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz

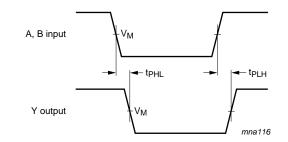
f_o = output frequency in MHz

C_L = output load capacitance in pF

V_{CC} = supply voltage in Volts

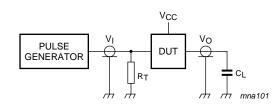
 $\sum (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs}$

12. Waveforms



For 74HC1G08-Q100: $V_M = 0.5 \times V_{CC}$; $V_I = GND$ to V_{CC} For 74HCT1G08-Q100: $V_M = 1.3$ V; $V_I = GND$ to 3.0 V





Test data is given in Table 8. Definitions for test circuit:

 C_L = Load capacitance including jig and probe capacitance

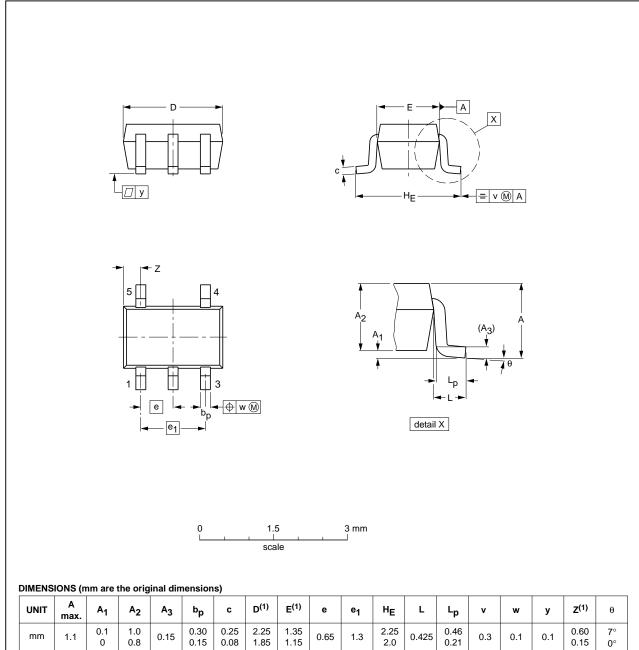
 R_T = Termination resistance should be equal to the output impedance Z_0 of the pulse generator

Fig 6. Test circuit for measuring switching times

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	HE	L	Lp	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.1 0	1.0 0.8	0.15	0.30 0.15	0.25 0.08	2.25 1.85	1.35 1.15	0.65	1.3	2.25 2.0	0.425	0.46 0.21	0.3	0.1	0.1	0.60 0.15	7° 0°

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

			EUROPEAN	ISSUE DATE
IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
	MO-203	SC-88A		-00-09-01 03-02-19
	IEC			MO COS COS COS COS COS COS COS COS COS CO

Package outline SOT353-1 (TSSOP5) Fig 7.

74HC_HCT1G08_Q100

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Plastic surface-mounted package; 5 leads

SOT753

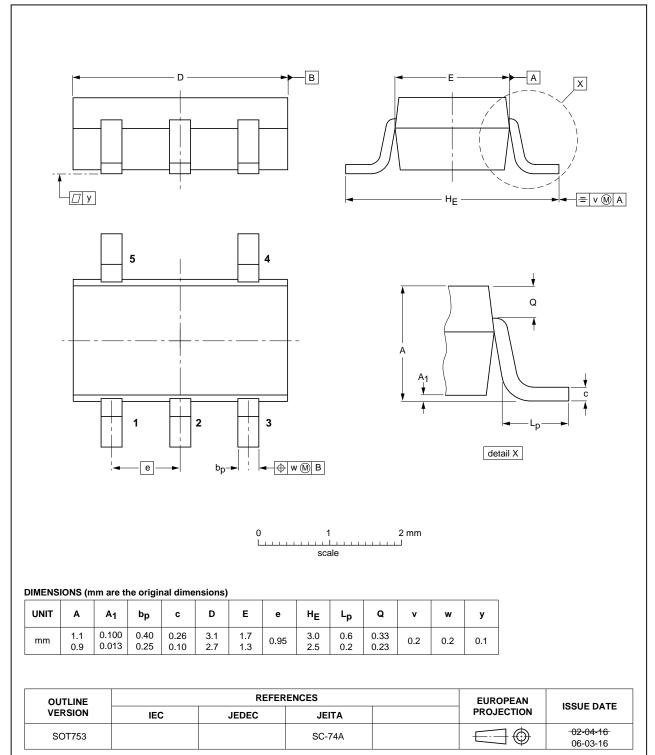


Fig 8. Package outline SOT753 (SC-74A)

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14. Abbreviations

Table 9. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
TTL	Transistor-Transistor Logic
НВМ	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
DUT	Device Under Test

15. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT1G08_Q100 v.2	20120816	Product data sheet	-	74HC_HCT1G08_Q100 v.1
Modifications:	 Added pi 	in 1 location note (Table 2)		
74HC_HCT1G08_Q100 v.1	20120605	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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NXP Semiconductors 74HC1G08-Q100; 74HCT1G08-Q100

2-input AND gate

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2-input AND gate

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